

74V2G07

TRIPLE BUFFER (OPEN DRAIN)

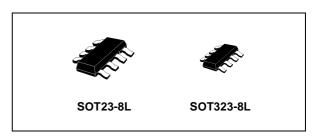
PRELIMINARY DATA

- HIGH SPEED: t_{PD} =3.7ns (TYP.) at V_{CC} = 5V
- LOW POWER DISSIPATION: $I_{CC} = 1\mu A(MAX.)$ at $T_A=25$ °C
- HIGH NOISE IMMUNITY: V_{NIH} = V_{NIL} = 28% V_{CC} (MIN.)
- POWER DOWN PROTECTION ON INPUT
- OPERATING VOLTAGE RANGE: V_{CC}(OPR) = 2V to 5.5V
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

The 74V2G07 is an advanced high-speed CMOS TRIPLE BUFFER (OPEN DRAIN) fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology.

The internal circuit is composed of 2 stages including buffer output, which provide high noise immunity and stable output.

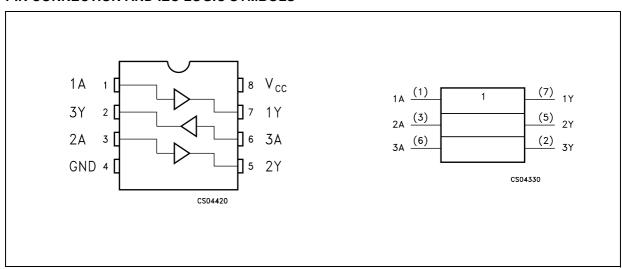


ORDER CODES

PACKAGE	T & R
SOT23-8L	74V2G07STR
SOT323-8L	74V2G07CTR

Power down protection is provided on input and 0 to 7V can be accepted on input with no regard to the supply voltage. This device can be used to interface 5V to 3V.

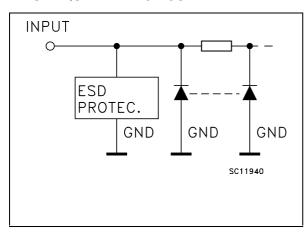
PIN CONNECTION AND IEC LOGIC SYMBOLS



November 2001 1/9

This is preliminary information on a new product now in development are or undergoing evaluation. Details subject to change without notice.

INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME QND FUNCTION
1, 3, 6	1A, 2A, 3A	Data Inputs
7, 5, 2	1Y, 2Y, 3Y	Data Outputs
4	GND	Ground (0V)
8	V _{CC}	Positive Supply Voltage

TRUTH TABLE

Α	Υ
L	L
Н	Z

Z: High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Ιο	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 5.5	V
V _I	Input Voltage	0 to 5.5	V
Vo	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) (V _{CC} = 3.3 ± 0.3 V) (V _{CC} = 5.0 ± 0.5 V)	0 to 100 0 to 20	ns/V ns/V

¹⁾ V_{IN} from 30% to 70% of V_{CC}

DC SPECIFICATIONS

		1	est Condition	Value							
Symbol	Parameter	V _{CC}		T	T _A = 25°C -40 to 85°C				-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	3.0 to 5.5		0.7V _{CC}			0.7V _{CC}		0.7V _{CC}		V
V _{IL}	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	3.0 to 5.5				0.3V _{CC}		0.3V _{CC}		0.3V _{CC}	V
V _{OL}	Low Level Output	2.0	I _O =50 μA		0.0	0.1		0.1		0.1	
	Voltage	3.0	I _O =50 μA		0.0	0.1		0.1		0.1	
		4.5	I _O =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I _O =4 mA			0.36		0.44		0.55	
		4.5	I _O =8 mA			0.36		0.44		0.55	
I _{OZ}	High Impedance Output Leakage Current	5.5	$V_I = V_{IH} \text{ or } V_{IL}$ $V_O = V_{CC} \text{ or GND}$			± 0.25		± 2.5		± 5	μΑ
I _I	Input Leakage Current	0 to 5.5	V _I = 5.5V or GND			± 0.1		± 1		± 1	μΑ
I _{CC}	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10		20	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$)

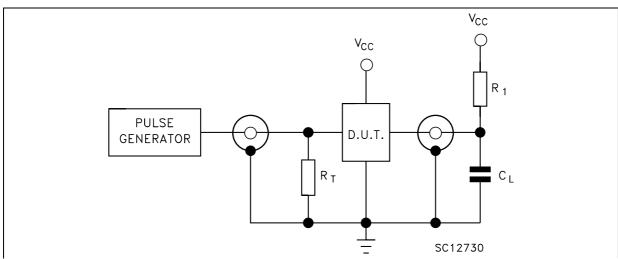
		Test Condition		Value								
Symbol	Parameter	V _{CC} C _L		T _A = 25°C			-40 to	85°C	-55 to 125°C		Unit	
	(V)	(V) (pF)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
t _{PZL}	Propagation Delay	3.3 ^(*)	15			4.8	7.7	1.0	9.0	1.0	10.0	
	Time	3.3 ^(*)	50			5.3	8.5	1.0	10.0	1.0	11.0	no
		5.0 ^(**)	15			3.7	5.5	1.0	6.5	1.0	7.5	ns
		5.0 ^(**)	50			4.2	7.5	1.0	8.5	1.0	9.5	
t_{PLZ}	Propagation Delay	3.3 ^(*)	50			7.5	10.5	1.0	11.5	1.0	12.5	nc
	Time	5.0 ^(**)	50			4.7	7.5	1.0	8.5	1.0	9.5	ns

CAPACITIVE CHARACTERISTICS

		Test Condition	Value							
Symbol Parameter			T,	T _A = 25°C			-40 to 85°C		-55 to 125°C	
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance			4	10		10		10	pF
C _{OUT}	Output Capacitance			5	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)			3						pF

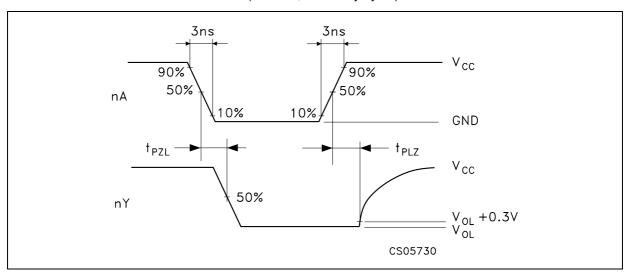
¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{CC(opr)} = C_{PD} x V_{CC} x f_{IN} + I_{CC}

TEST CIRCUIT



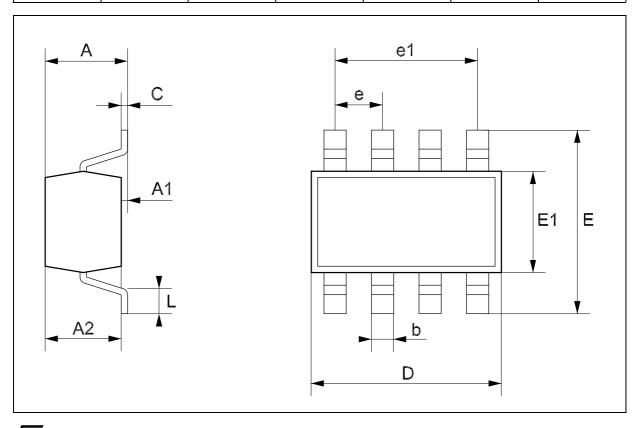
 C_L = 15/50pF or equivalent (includes jig and probe capacitance) R_1 = 1K Ω or equivalent R_T = Z_{OUT} of pulse generator (typically 50 Ω)

WAVEFORM: PROPAGATION DELAY (f=1MHz; 50% duty cycle)



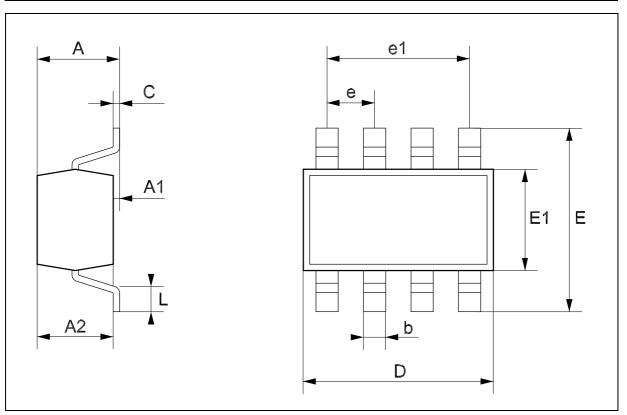
SOT23-8L MECHANICAL DATA

DIM		mm.				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	0.90		1.45	35.4		57.1
A1	0.00		0.15	0.0		5.9
A2	0.90		1.30	35.4		51.2
b	0.22		0.38	8.6		14.9
С	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	2.60		3.00	102.3		118.1
E1	1.50		1.75	59.0		68.8
е	0	.65			25.6	
e1		1.95			76.7	
L	0.35		0.55	13.7		21.6



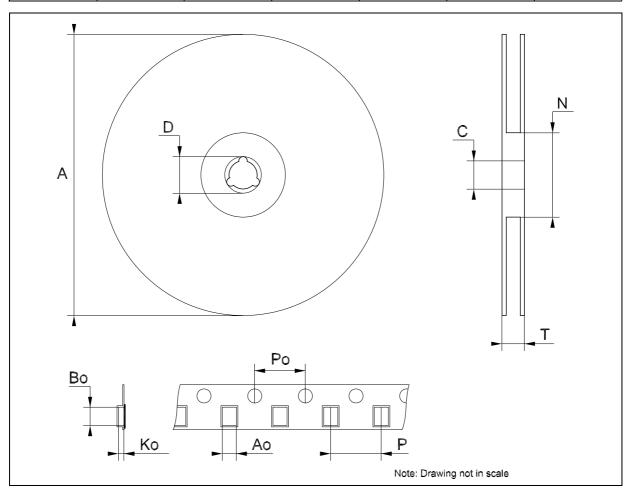
SOT323-8L MECHANICAL DATA

DIM.		mm.		mils			
DINI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А	0.80		1.10	31.5		43.3	
A1	0.00		0.10	0.0		3.9	
A2	0.80		1.00	31.5		34.9	
b	0.13		0.28	5.1		11.0	
С	0.10		0.18	3.9		7.1	
D	1.80		2.20	70.9		86.6	
E	1.80		2.40	70.9		94.5	
E1	1.15		1.35	45.3		53.1	
е		0.5			19.7		
e1		1.5			59.0		
L	0.10		0.30	3.9		11.8	

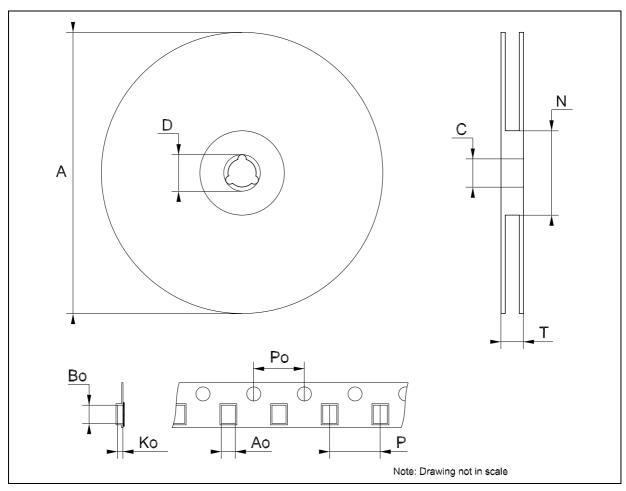


Tape & Reel SOT23-xL MECHANICAL DATA

DIM		mm.		inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А			180			7.086	
С	12.8	13.0	13.2	0.504	0.512	0.519	
D	20.2			0.795			
N	60			2.362			
Т			14.4			0.567	
Ao	3.13	3.23	3.33	0.123	0.127	0.131	
Во	3.07	3.17	3.27	0.120	0.124	0.128	
Ko	1.27	1.37	1.47	0.050	0.054	0.0.58	
Ро	3.9	4.0	4.1	0.153	0.157	0.161	
Р	3.9	4.0	4.1	0.153	0.157	0.161	



DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	175	180	185	6.889	7.086	7.283
С	12.8	13	13.2	0.504	0.512	0.519
D	20.2			0.795		
N	59.5	60	60.5		2.362	
Т			14.4			0.567
Ao		2.25			0.088	
Во		2.7			0.106	
Ko		1.2			0.047	
Po	3.98	4	4.2	0.156	0.157	0.165
Р	3.98	4	4.2	0.156	0.157	0.165



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